

Features

- High Blocking Voltage with Low On-Resistance
- High Speed Switching with Low Capacitances
- Easy to Parallel and Simple to Drive
- Avalanche Ruggedness
- Halogen Free, RoHS Compliant

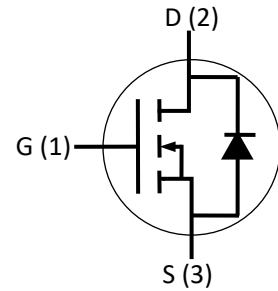
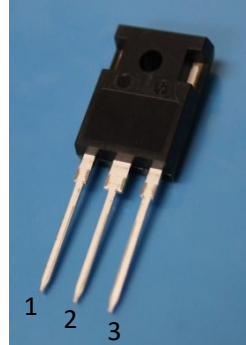
Benefits

- Higher System Efficiency
- Reduced Cooling Requirements
- Increased Power Density
- Increased System Switching Frequency

Applications

- Solar Inverters
- Switch Mode Power Supplies
- High Voltage DC/DC Converters
- Battery Chargers
- Motor Drives
- Pulsed Power applications

Package



Maximum Ratings ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	650	V	$V_{GS}=0V, I_D=100\mu A$	
V_{GSmax}	Gate - Source Voltage	-8/+22	V	Absolute maximum values	
V_{GSop}	Gate - Source Voltage	-5/+18	V	Recommended operational values	
I_D	Continuous Drain Current	40	A	$V_{GS}=20V, T_C=25^\circ\text{C}$	
		29		$V_{GS}=20V, T_C=100^\circ\text{C}$	
I_{DM}	Pulse Drain Current	90	A	Pulse width limited by T_{jmax}	
P_D	Power Dissipation	150	W	$T_C=25^\circ\text{C}, T_J=175^\circ\text{C}$	Fig. 11
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +175	$^\circ\text{C}$		

Electrical Characteristics

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	650			V	$V_{GS}=0V, I_D=100\mu A$	
$V_{GS(th)}$	Gate Threshold Voltage	2.0	3.2	4.0	V	$V_{GS}=V_{DS}, I_{DS}=5mA, T_C=25^\circ C$	Fig. 6
			2.3			$V_{GS}=V_{DS}, I_{DS}=5mA, T_C=175^\circ C$	
I_{DSS}	Zero Gate Voltage Drain Current		1	100	μA	$V_{DS}=650V, V_{GS}=0V$	
I_{GSS}	Gate-Source Leakage Current		50	200	nA	$V_{GS}=18V, V_{DS}=0V$	
$R_{DS(on)}$	Drain-Source on-state Resistance		45	65	m Ω	$V_{GS}=18V, I_D=20A, T_C=25^\circ C$	Fig. 4
			75			$V_{GS}=18V, I_D=20A, T_C=175^\circ C$	
g_{fs}	Transconductance		12		S	$V_{DS}=20V, I_D=20A, T_J=25^\circ C$	Fig. 5
			11		S	$V_{DS}=20V, I_D=20A, T_J=175^\circ C$	
C_{iss}	Input Capacitance		1100		pF	$V_{GS}=0V, V_{DS}=400V, f=1MHz$ $V_{AC}=25mV$	Fig. 9
C_{oss}	Output Capacitance		56				
C_{rss}	Reverse Transfer Capacitance		15				
E_{ON}	Turn-On Switching Energy		110		μJ	$V_{DS}=400V, V_{GS}=-5/18V, I_D=20A,$ $R_{G(ext)}=0\Omega$	
E_{OFF}	Turn-Off Switching Energy		32				
$t_{d(on)}$	Turn-On Delay Time		15		ns	$V_{DD}=400V, V_{GS}=-0/20V$ $I_D=20A, \text{Timing relative to } V_{DS}$	
t_r	Rise Time		45				
$t_{d(off)}$	Turn-Off Delay Time		13				
t_f	Fall Time		10				
$R_{G(int)}$	Internal Gate Resistance		6.0		Ω	$f=1MHz, V_{AC}=25mV$	
Q_{gs}	Gate to Source Charge		21		nC	$V_{DD}=400V, V_{GS}=-0/20V$ $I_D=20A$	Fig. 10
Q_{gd}	Gate to Drain Charge		14				
Q_g	Total Gate Charge		75				

Reverse Diode Characteristics

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	3.4		V	$V_{GS}=-5V, I_{SD}=10A, T_J=25^\circ C$	Fig. 7
		3.2		V	$V_{GS}=-5V, I_{SD}=10A, T_J=175^\circ C$	Fig. 8
I_S	Continuous Diode Forward Current		30	A	$T_C=25^\circ C$	
t_{rr}	Reverse Recovery time	20		ns	$V_{GS}=-5V, I_{SD}=20A, V_R=400V,$ $dif/dt=1200A/\mu s;$	
Q_{rr}	Reverse Recovery Charge	65		nC		
I_{rrm}	Peak Reverse Recovery Current	8		A		

Thermal Characteristics

Symbol	Parameter	Typ.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	0.95	$^\circ C/W$		Fig. 12
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient	35			

Typical Performance

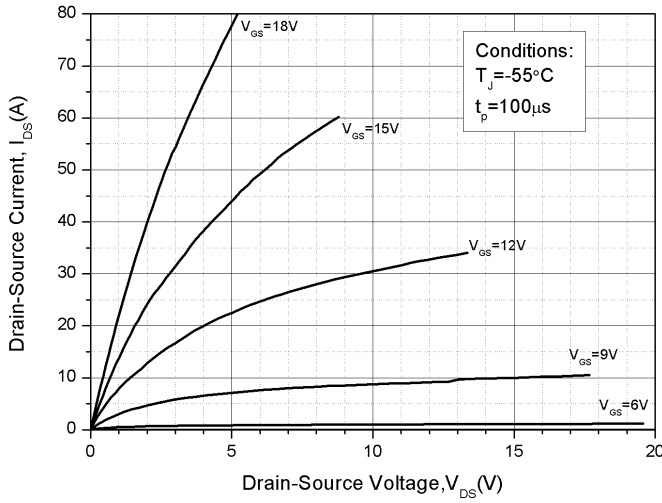


Figure 1. Output Characteristics $T_j = -55\text{ }^\circ\text{C}$

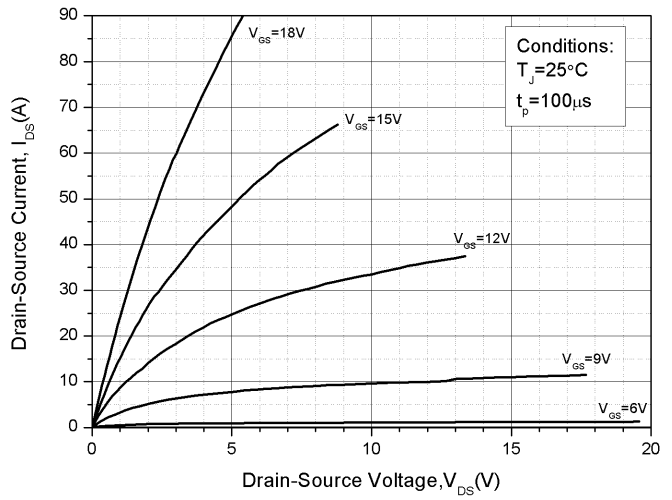


Figure 2. Output Characteristics $T_j = 25\text{ }^\circ\text{C}$

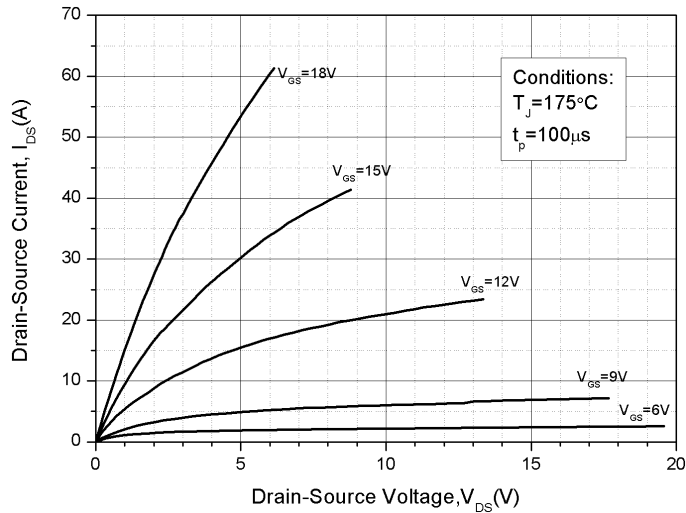


Figure 3. Output Characteristics $T_j = 175\text{ }^\circ\text{C}$

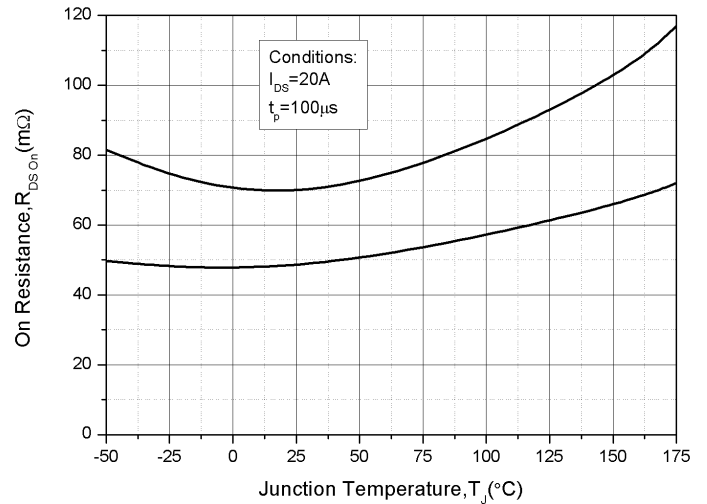


Figure 4. On-Resistance For Various Gate Voltage

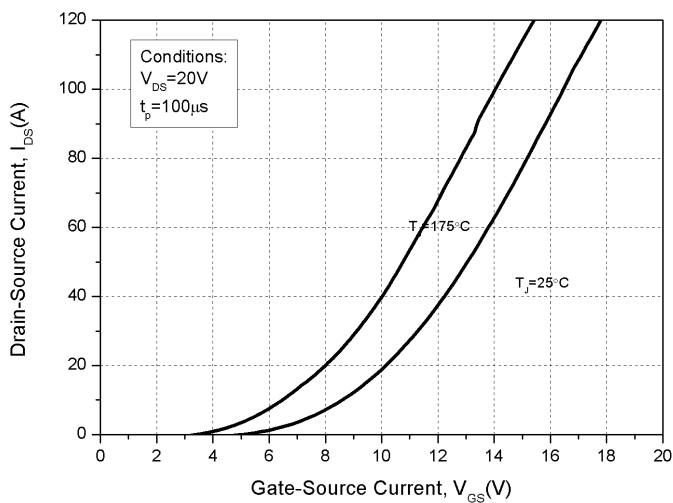


Figure 5. Transfer Characteristic for Various Junction Temperatures

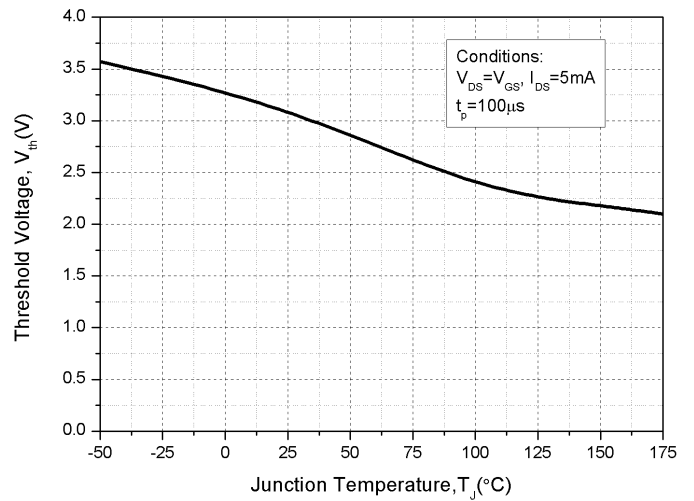


Figure 6. Threshold Voltage vs. Temperature

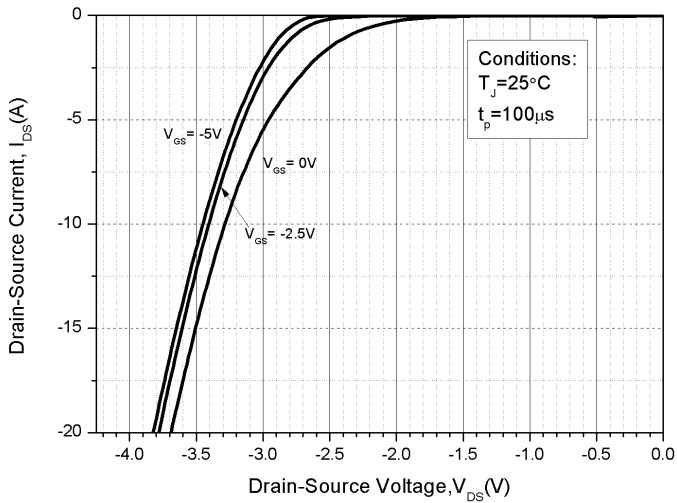


Figure 7. Body Diode Characteristics, $T_J = 25\text{ }^\circ\text{C}$

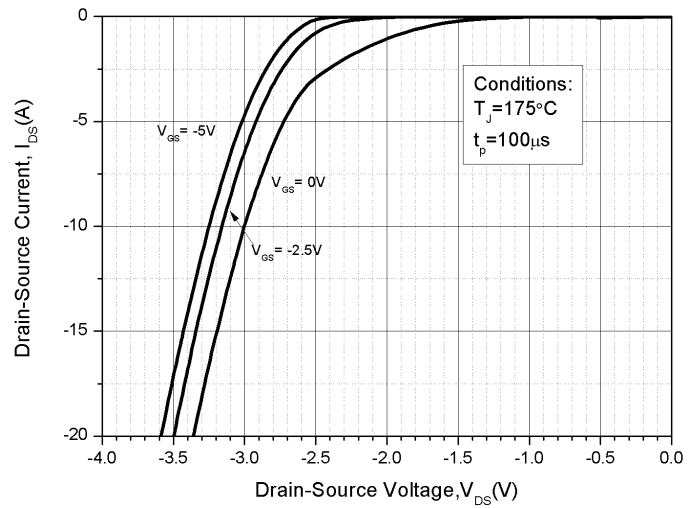


Figure 8. Body Diode Characteristics, $T_J = 175\text{ }^\circ\text{C}$

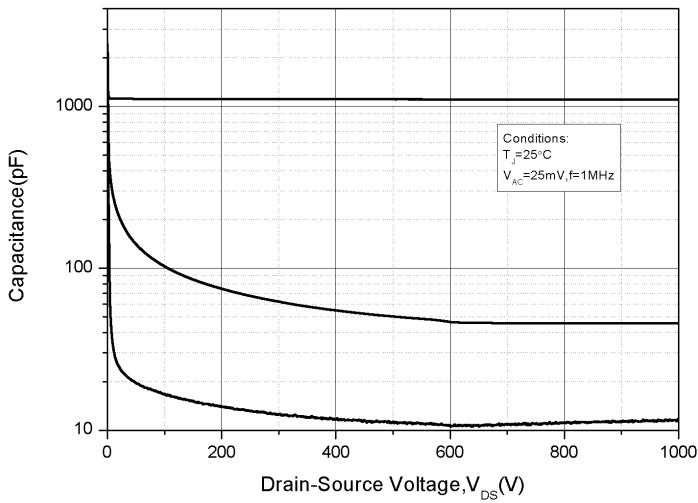


Figure 9. Capacitances vs. Drain-Source Voltage

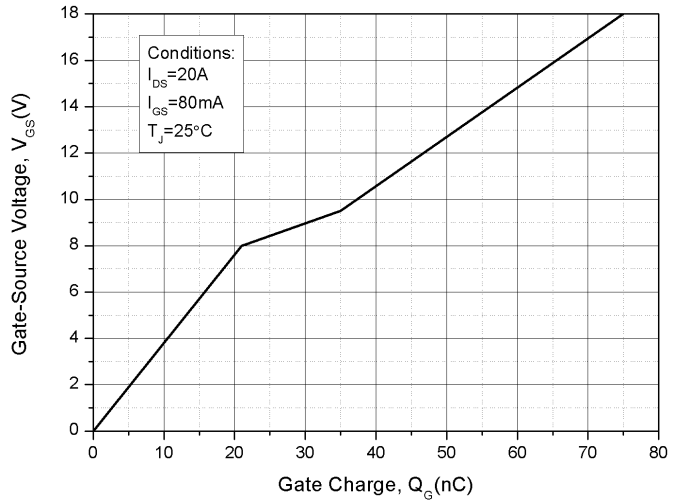


Figure 10. Gate Charge Characteristics

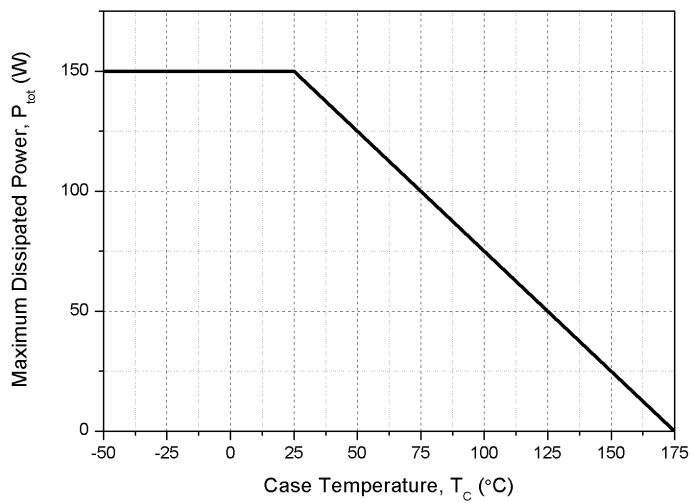


Figure 11. Power Dissipation Derating

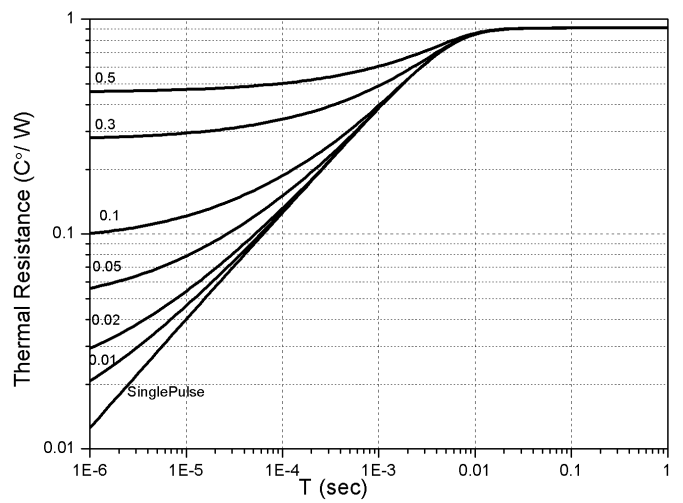
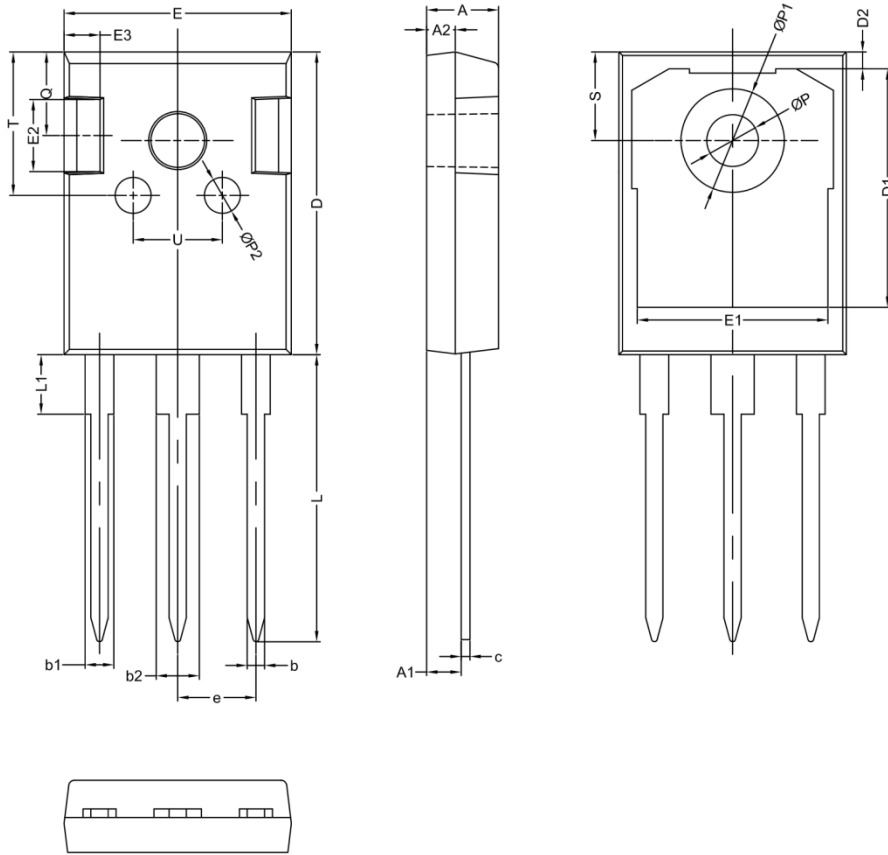


Figure 12. Transient Thermal Impedance

Package Dimensions: TO-247-3L



符号	机械尺寸/mm		
	最小值	典型值	最大值
A	4.80	5.00	5.20
A1	2.21	2.41	2.61
A2	1.90	2.00	2.10
b	1.10	1.20	1.35
b1		2.00	
b2		3.00	
c	0.55	0.60	0.75
D	20.80	21.00	21.20
D1		16.55	
D2		1.20	
E	15.60	15.80	16.0
E1		13.30	
E2		5.00	
E3		2.50	
e		5.44	
L	19.42	19.92	20.42
L1		4.13	
P	3.50	3.60	3.70
P1	-	-	7.40
P2		2.50	
Q		5.80	
S	6.05	6.15	6.25
T		10.00	
U		6.20	